

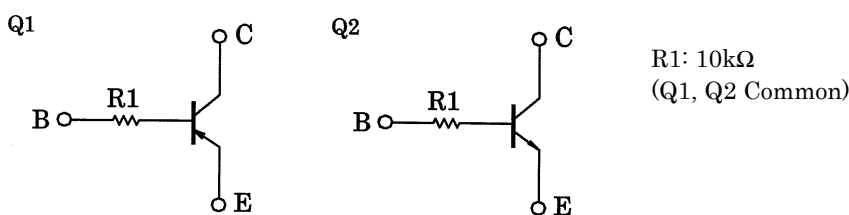
TOSHIBA Transistor  
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

## RN4911

Switching, Inverter Circuit, Interface Circuit  
And Driver Circuit Applications

- Including two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

### Equivalent Circuit and Bias Resister Values



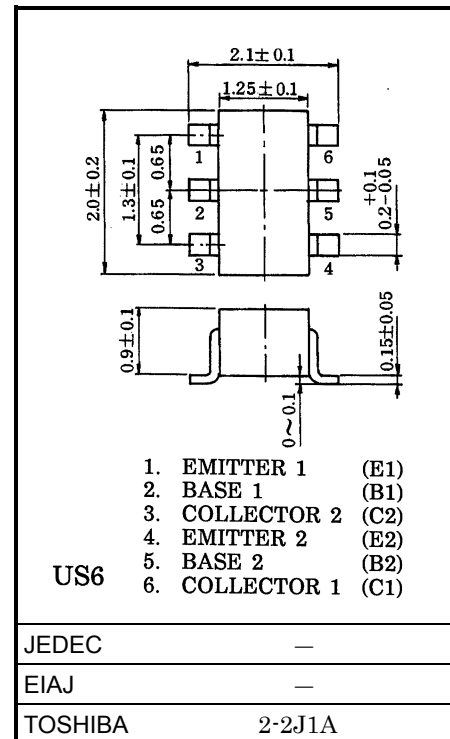
### Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA

### Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA

Unit in mm



Weight: 6.8mg

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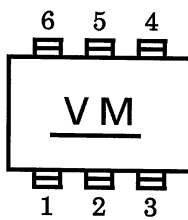
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**Q1, Q2 Common Maximum Ratings (Ta = 25°C)**

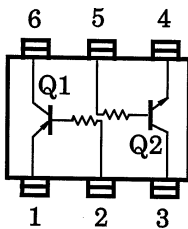
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> *	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

\* Total rating

**Marking**



**Equivalent Circuit (Top View)**



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- The information contained herein is subject to change without notice.

**Q1 Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	—	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
Emitter cut-off current	$I_{EBO}$	—	$V_{EB} = -5V, I_C = 0$	—	—	-100	mA
DC current gain	$h_{FE}$	—	$V_{CE} = -5V, I_C = -1mA$	120	—	400	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Transition frequency	$f_T$	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector output capacitance	$C_{ob}$	—	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	6	pF

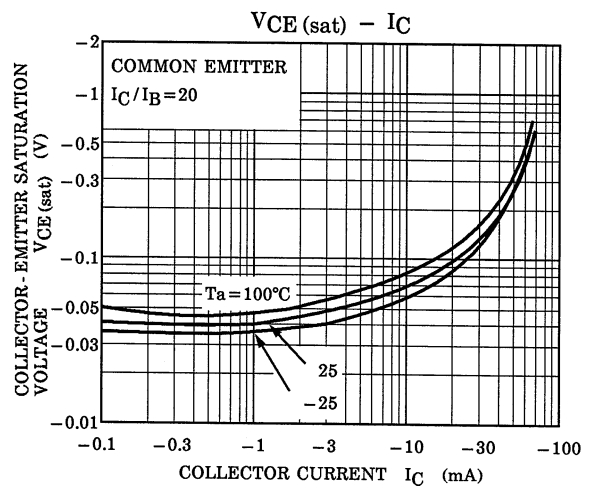
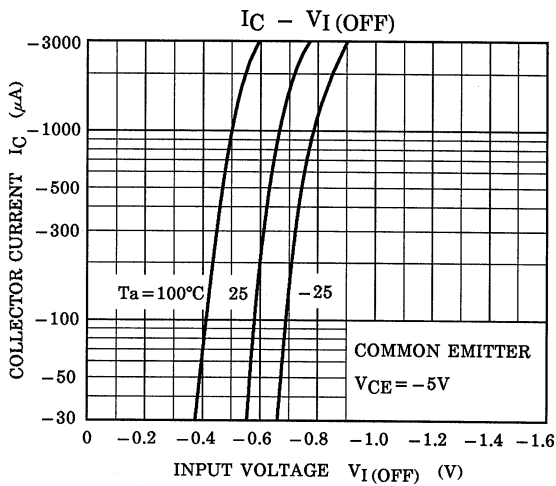
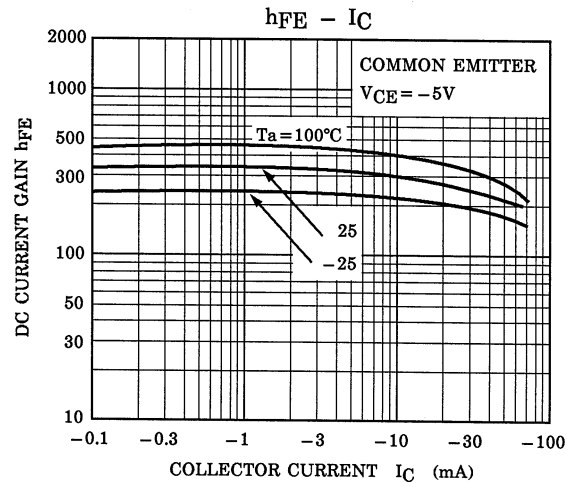
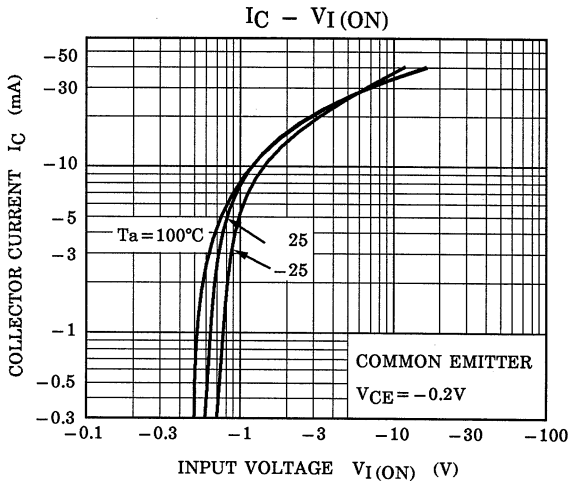
**Q2 Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	—	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
Emitter cut-off current	$I_{EBO}$	—	$V_{EB} = 5V, I_C = 0$	—	—	100	mA
DC current gain	$h_{FE}$	—	$V_{CE} = 5V, I_C = 1mA$	120	—	700	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Transition frequency	$f_T$	—	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector output capacitance	$C_{ob}$	—	$V_{CB} = 10V, I_E = 0, f = 1 MHz$	—	3	6	pF

**Q1, Q2 Common Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	—	7	10	13	kΩ

Q1



Q2

